

NPN SILICON PLANAR MEDIUM POWER TRANSISTOR

ZTX649

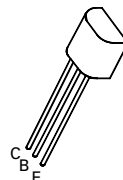
ISSUE 2 – APRIL 94

FEATURES

- * 25 Volt V_{CE0}
- * 2 Amp continuous current
- * Low saturation voltage
- * $P_{tot}=1$ Watt

APPLICATIONS

- * Motor driver
- * DC-DC converters



E-Line
TO92 Compatible

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	35	V
Collector-Emitter Voltage	V_{CEO}	25	V
Emitter-Base Voltage	V_{EBO}	5	V
Peak Pulse Current	I_{CM}	6	A
Continuous Collector Current	I_C	2	A
Power Dissipation at $T_{amb}=25^{\circ}C$ derate above $25^{\circ}C$	P_{tot}	1 5.7	W mW/°C
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +200	°C

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	35			V	$I_C=100\mu A$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	25			V	$I_C=10mA^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5			V	$I_E=100\mu A$
Collector Cut-Off Current	I_{CBO}			0.1 10	μA	$V_{CB}=30V$ $V_{CB}=30V, T_{amb}=100^{\circ}C$
Emitter Cut-Off Current	I_{EBO}			0.1	μA	$V_{EB}=4V$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		0.12 0.23	0.3 0.5	V	$I_C=1A, I_B=100mA^*$ $I_C=2A, I_B=200mA^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		0.9	1.25	V	$I_C=1A, I_B=100mA^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		0.8	1	V	$I_C=1A, V_{CE}=2V^*$
Static Forward Current Transfer Ratio	h_{FE}	70 100 75 15	200 200 150 50	300		$I_C=50mA, V_{CE}=2V^*$ $I_C=1A, V_{CE}=2V^*$ $I_C=2A, V_{CE}=2V^*$ $I_C=6A, V_{CE}=2V^*$
Transition Frequency	f_T	150	240		MHz	$I_C=100mA, V_{CE}=5V$ $f=100MHz$

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ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated).

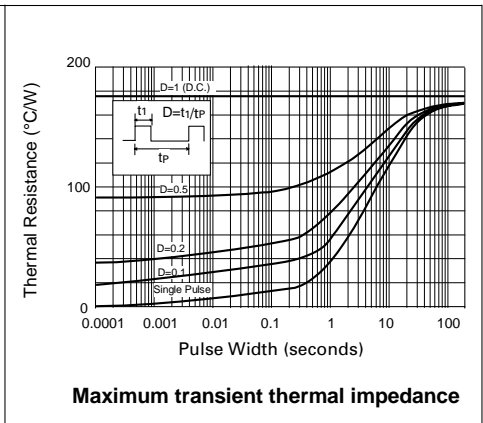
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Output Capacitance	C_{obo}		25	50	pF	$V_{CB}=10\text{V}$ $f=1\text{MHz}$
Switching Times	t_{on}		55		ns	$I_C=500\text{mA}$, $V_{CC}=10\text{V}$ $I_{B1}=I_{B2}=50\text{mA}$
	t_{off}		300		ns	

*Measured under pulsed conditions. Pulse Width=300 μs . Duty cycle $\leq 2\%$

THERMAL CHARACTERISTICS

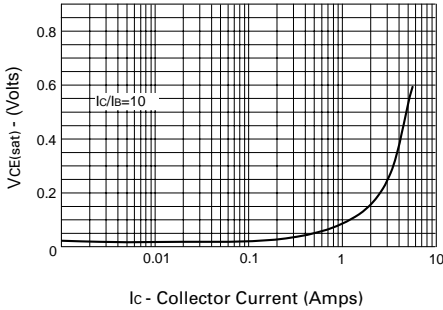
PARAMETER	SYMBOL	MAX.	UNIT
Thermal Resistance: Junction to Ambient ₁	$R_{th(j-amb)1}$	175	$^{\circ}\text{C/W}$
Junction to Ambient ₂	$R_{th(j-amb)2}$ †	116	$^{\circ}\text{C/W}$
Junction to Case	$R_{th(j-case)}$	70	$^{\circ}\text{C/W}$

† Device mounted on P.C.B. with copper equal to 1 sq. Inch minimum.

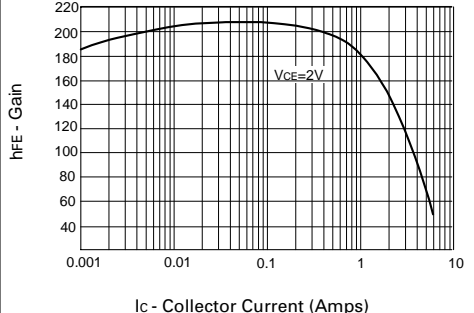


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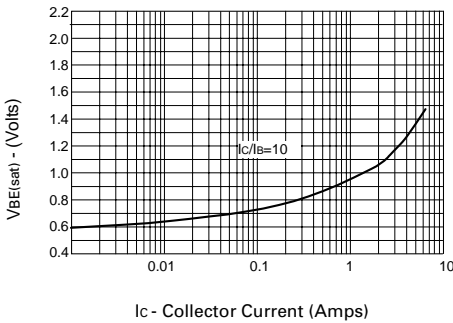
TYPICAL CHARACTERISTICS



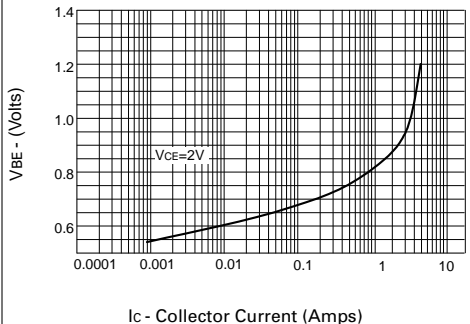
$V_{CE(sat)}$ v I_C



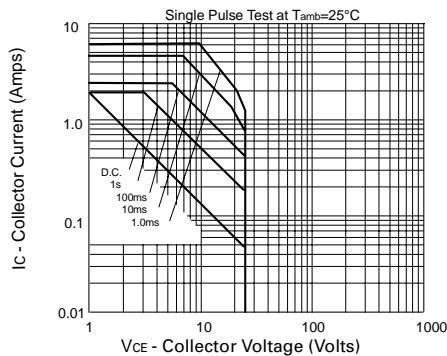
hFE v I_C



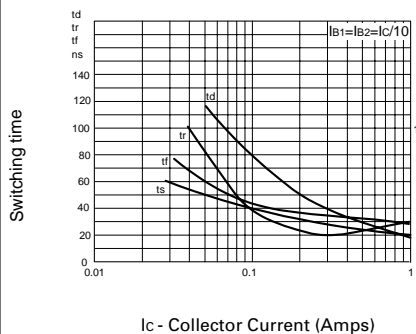
$V_{BE(sat)}$ v I_C



$V_{BE(on)}$ v I_C



Safe Operating Area



Switching Speeds